INFORMATION DISCLOSURE CIDATION (Use several sheets if necessary)					Docket Number (Optional) YOR920030293US1 (16818) Applicant(s)		Application Number 10/674,647		
						JUN 3 0 2005 F			
				<i>Ş</i> }	September 30, 20	03		753	1762
U.S. ATENT DOCUMENTS									
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS		DATE
								IF APPR	OPRIATE
				,			 		
		-							
<u></u>				·]		
U.S. PATENT APPLICATION PUBLICATIONS *EXAMINER STUDIES ATTE									
INITIAL	REF	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS		DATE OPRIATE
/MLP/		US 2002/0086463 A1	07/04/02	Houston, et al					
/MLP/		US 2004/0126985 A1	07/01/04	Bendernagel, et al					
			·						
FOREIGN PATENT DOCUMENTS									
	REF	F DOCUMENT NUMBER DATE			COUNTRY	CLASS	SUBCLASS	Tran YES	station NO
/MLP/		9-64323	07/03/97	Japan					X
/MLP/		WO 2005/034209 A2	04/15/05 PCT				in Engl		1
								•	
-		· · · · · · · · · · · · · · · · · · ·							
			OTHER D	OCUMENT	ΓS (Including Author,	Title, Date, Po	ertinent Pages, Et	c.)	
/MLP/ Matsumura, et al., "Technological innovation in low-dose SIMOX wafers fabricated by an internal thermal oxidation process", 2002 Elsevier Science B.V., Microelectronic Engineering 66 (2003), pp. 400-414								n (ITOX)	
/ WILI /		all odd-numb							
		1					-		
		Ma Sa ST	6 6 1 Ac	HT.					
EXAMINER /Marianne L. Padgett/					DATE CONSIDER 05/18/2007				
EXAMINES	R: Initia	Il if citation considered, whether o	r not citation is in o	conformanc pplicant.		 aw line throu	gh citation if not	in conform	ance and